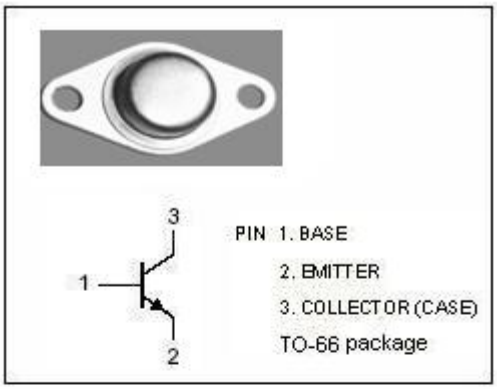
isc Silicon NPN Power Transistor — 2SD144

DESCRIPTION

- DC Current Gain -h_{FE} = 40(Min)@ I_C= 1A
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)\,CEO}$= 50V(Min)
- With TO-66 Package
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

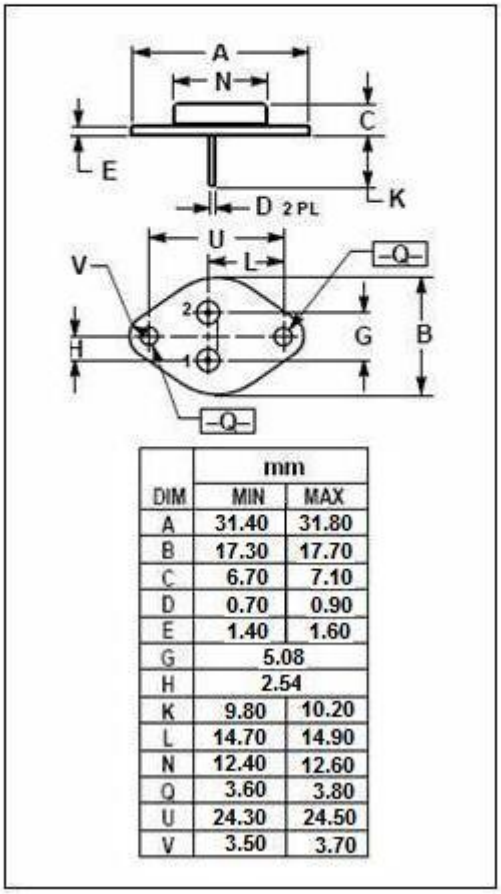


APPLICATIONS

- Designed for use in power amplifier applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	2.0	A
I_{CM}	Collector Current-Peak	3.0	A
I_B	Base Current	1.0	A
P_C	Collector Power Dissipation@T_C=25℃	15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.50	3.70

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 20mA ; I_B= 0	50		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 3A; I_B= 0.3A		1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 3A; I_B= 0.3A		1.8	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 100V; V_{EB}= 0		0.1	mA
I_{CEO}	Collector Cutoff Current	V_{CE}= 50V; I_B= 0		0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0		0.1	mA
h_{FE}	DC Current Gain	I_C= 1A ; V_{CE}= 2V	40	200	
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A ; V_{CE}= 10V	10		MHz